

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently amended) A light emitting diode, comprising:
 - a semiconductor substrate;
 - a light-emitting region including an active layer provided between a first conductivity type cladding layer formed on the semiconductor substrate and a second conductivity type cladding layer;
 - a transparent conductive film made of a metal oxide and located over the light-emitting region;
 - a first electrode formed on the upper side of the transparent conductive film;
 - a second electrode formed on the whole or a part of the bottom of the semiconductor substrate; and
 - a layer for preventing exfoliation of the transparent conductive film, the preventing layer being made of a compound semiconductor containing at least aluminum and located between the light-emitting region and the transparent conductive film, the preventing layer having a high carrier concentration; and
 - an undoped layer or a low carrier concentration layer formed between the active layer and the second conductivity type cladding layer.
2. (Original) The light emitting diode as defined in claim 1, wherein:
 - the preventing layer contains a conductivity type determination impurity at a concentration of $1 \times 10^{19} \text{ cm}^{-3}$ or higher.
3. (Original) The light emitting diode as defined in claim 1, wherein:
 - the preventing layer has a film thickness of 300 nm or less.
4. (Original) The light emitting diode as defined in claim 2, wherein:
 - the preventing layer has a film thickness of 300 nm or less.

5. (Original) The light emitting diode as defined in claim 1, wherein:
the transparent conductive film is made of indium tin oxide.
6. (Original) The light emitting diode as defined in claim 2, wherein:
the transparent conductive film is made of indium tin oxide.
7. (Original) The light emitting diode as defined in claim 1, wherein:
the preventing layer is made of an arsenic compound.
8. (Original) The light emitting diode as defined in claim 2, wherein:
the preventing layer is made of an arsenic compound.
9. (Original) The light emitting diode as defined in claim 1, wherein:
the light-emitting region is made of $(\text{Al}_X\text{Ga}_{1-X})_Y\text{In}_{1-Y}\text{P}$ ($0 \leq X \leq 1$, $0 \leq Y \leq 1$).
10. (Original) The light emitting diode as defined in claim 2, wherein:
the light-emitting region is made of $(\text{Al}_X\text{Ga}_{1-X})_Y\text{In}_{1-Y}\text{P}$ ($0 \leq X \leq 1$, $0 \leq Y \leq 1$).
11. (Original) The light emitting diode as defined in claim 1, wherein:
the preventing layer is an AlGaAs layer having a bandgap which is smaller than that of the active layer; and
the AlGaAs layer is made of $\text{Al}_X\text{Ga}_{1-X}\text{As}$ ($0.01 \leq X \leq 0.43$).
12. (Currently amended) The light emitting diode as defined in claim 1, wherein:
the preventing AlGaAs layer has a carrier concentration of $1 \times 10^{19} \text{ cm}^{-3}$ or higher.
13. (Original) The light emitting diode as defined in claim 11, wherein:
the AlGaAs layer has a carrier concentration of $1 \times 10^{19} \text{ cm}^{-3}$ or higher.
14. (Currently amended) The light emitting diode as defined in claim 1, wherein:
the preventing AlGaAs layer is added with at least one of Zn, Be, and Mg.
15. (Original) The light emitting diode as defined in claim 11, wherein:
the AlGaAs layer is added with at least one of Zn, Be, and Mg.

16. (Currently amended) The light emitting diode as defined in claim 1, wherein:
the preventing AlGaAs layer is added with at least one of Zn, Be and Mg, and C; and
C is autodoped.
17. (Original) The light emitting diode as defined in claim 11, wherein:
the AlGaAs layer is added with at least one of Zn, Be and Mg, and C; and
C is autodoped.
18. (Currently amended) The light emitting diode as defined in claim 1, wherein:
the preventing AlGaAs layer is formed at a growth temperature of 600°C or lower.
19. (Original) The light emitting diode as defined in claim 11, wherein:
the AlGaAs layer is formed at a growth temperature of 600°C or lower.
20. (Currently amended) The light emitting diode as defined in claim 1, wherein:
the preventing AlGaAs layer is formed at a V/III ratio in raw materials of 50 or less at
the time of growth.
21. (Original) The light emitting diode as defined in claim 11, wherein:
the AlGaAs layer is formed at a V/III ratio in raw materials of 50 or less at the time of
growth.
22. (Original) The light emitting diode as defined in claim 11, wherein:
the transparent conductive film is made of indium tin oxide.
23. (Original) The light emitting diode as defined in claim 11, wherein:
the light-emitting region is made of $(\text{Al}_X\text{Ga}_{1-X})_Y\text{In}_{1-Y}\text{P}$ ($0 \leq X \leq 1, 0 \leq Y \leq 1$).